

Rad Hard MOSFET Solutions Selector Guide



MOSFETs	BVDSS	RDS(on)	ID	Gate Charge	TID Level	Die Size	Package	Screening
Units	(V)	(mΩ)	(A)	(nC)	krads(Si)			
RAD7110-NCx	100	220	6.5	12	100	1	Bare Die	Proto, EM, Space
RAD7110-NFx	100	250	6.5	12	100	1	TO-39	Proto, EM, Space
RAD7110-NNNx	100	220	6.5	12	100	1	SMD 0.22	Proto, EM, Space
RAD7130-NCx	100	50	22	50	100	3	Bare Die	Proto, EM, Space
RAD7130-NFx	100	80	12	50	100	3	TO-39	Proto, EM, Space
RAD7130-NNJx	100	60	22	50	100	3	SMD 0.5	Proto, EM, Space
RAD7130-NNPx	100	60	22	50	100	3	SMD 0.3	Proto, EM, Space
RAD7130-NYx	100	80	22	50	100	3	TO-257AA	Proto, EM, Space
RAD7160-NCx	100	12	60	150	100	6	Bare Die	Proto, EM, Space
RAD7160-NNAx	100	18	60	150	100	6	SMD 2	Proto, EM, Space
RAD7160-NMx	100	18	60	150	100	6	TO-254AA	Proto, EM, Space
RAD7114-NCx	150	400	2	13	100	1	Bare Die	Proto, EM, Space
RAD7114-NFx	150	450	2	13	100	1	TO-39	Proto, EM, Space
RAD7134-NCx	150	100	19	50	100	3	Bare Die	Proto, EM, Space
RAD7134-NNJx	150	110	19	50	100	3	SMD 0.5	Proto, EM, Space
RAD7134-NYx	150	110	19	50	100	3	TO-257AA	Proto, EM, Space
RAD7164-NCx	150	24	45	150	100	6	Bare Die	Proto, EM, Space
RAD7164-NNAx	150	27	45	150	100	6	SMD 2	Proto, EM, Space
RAD7164-NMx	150	27	45	150	100	6	TO-254AA	Proto, EM, Space
RAD7210-NCx	200	630	2	13	100	1	Bare Die	Proto, EM, Space
RAD7210-NFx	200	700	2	13	100	1	TO-39	Proto, EM, Space
RAD7230-NCx	200	130	12	50	100	3	Bare Die	Proto, EM, Space
RAD7230-NFx	200	180	8	50	100	3	TO-39	Proto, EM, Space
RAD7230-NNJx	200	150	12	50	100	3	SMD 0.5	Proto, EM, Space
RAD7230-NYx	200	150	12	50	100	3	TO-257AA	Proto, EM, Space
RAD7260-NCx	200	34	50	150	100	6	Bare Die	Proto, EM, Space
RAD7260-NNAx	200	34	50	150	100	6	SMD 2	Proto, EM, Space
RAD7260-NMx	200	34	50	150	100	6	TO-254AA	Proto, EM, Space
RAD7214-NCx	250	880	2.5	15	100	1	Bare Die	Proto, EM, Space
RAD7214-NFx	250	1000	2.5	15	100	1	TO-39	Proto, EM, Space
RAD7214-NQx	250	1000	2.5	15	100	1	Quad LCC-28	Proto, EM, Space

Units exhibit immunity to SEGR and SEB when tested at full rated drain potential and in the off-state at an LET up to 84MeV-cm²/mg. x = P for Prototype; the die is functional and tested to room temp and may have visual defects. E is a flight die, tested at 3 temps with no screening or QCI. S for Class S.

MOSFET Numbering

RAD	7	1	1	0	N	M			P	X
	TID Level	Breakdown	Die Size	Voltage Adder	Channel Type	Package			Screening	Technology
	7-100krad (Si)	1 - 100V	1 - Size 1	0 - None	N - N Type	C - Bare Die	Q - LCC 28 Pin	NM - SMD 0.2	P - Proto	Reserved
		2 - 200V	2 - Size 2	3 - 30V	P - P Type	F - TO-39	Y - TO-257	NN - SMD 0.22	E - EM	
			3 - Size 3	5 - 50V	M - Mixed	G - DIP 14 Pin	NA - SMD 2	NP - SMD 0.3	S - Space	
			4 - Size 4			M - TO-254AA	NJ - SMD 0.5			
			6 - Size 6							

Size 1 - 99mils x 80mils, Size 2 - 125mils x 85 mils, Size 3 - 126mils x 182mils, Size 4 - 227mils x 170mils, Size 6 - 279mils x 324mils